

Amendments to the Specification:

Please replace the abstract with the amended abstract on the following page:

The invention relates to a A trench MOSFET with drain (8), ~~drift~~ drift region (10) body (12) and source (14). In order to improve the figure of ~~merit~~ merit for use of the MOSFET as control and sync FETs, the trench (20) is partially filled with dielectric (24) adjacent to the drift region (10) and a graded doping profile is used in the ~~drift region~~ (+0) drift region (10).